Part Number	Customer

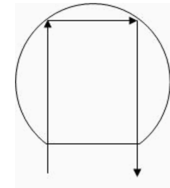
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	Customer Supplied
	2.0	Primary Flat Orientation	{110}+/- 1.0 degree	Customer Supplied
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Customer Supplied
	4.0	Secondary Flat Orientation	none	Customer Supplied
	5.0	Overall Thickness	510.00 +/- 12.50 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00µm	Guaranteed by Process
	7.0	Bow	<80.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<80.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	FZ	Customer Supplied
	12.0	Handle Orientation	{100} +/- 0.5 degree	Customer Supplied
	13.0	Handle Thickness	400.00 +/- 10.00 µm	Customer Supplied
	14.0	Handle Doping Type	N	Customer Supplied
	15.0	Handle Dopant	Phosphorous	Customer Supplied
	16.0	Handle Resistivity	>300 Ohmcm	Customer Supplied
	17.0	Backside Finish	Polished with IceMOS laser mark and oxide	Guaranteed by process
BuriedOxide	18.0	Oxide Type	Thermal	Guaranteed by process
	19.0	Oxide Thickness	2,000.00 +/- 150.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle wafer	Guaranteed by process
DeviceSilicon	21.0	Device Growth Method	FZ	Customer Supplied
	22.0	Device Orientation	{100} +/- 0.5 degree	Customer Supplied
	23.0	Nominal Thickness	110.00 +/- 2.00 µm	FTIR, 100% 9-Pt (note3 and 4)
	24.0	Distance to device silicon edge from wafer edge	1.5mm +/- 0.5mm	Edge Defined - Grinding, terrace edge etched.
	25.0	Device Doping Type	P	Customer Supplied
	26.0	Device Dopant	Boron	Customer Supplied
	27.0	Device Resistivity	>10000 Ohmcm	Customer Supplied
	28.0	Buried Layer Implant	Species = Boron, Energy = 40 KeV, Dose = 1e15 at/cm2, Screen Ox = 240A	Ion Implant Vendor
	29.0	Voids	none	Bright Light 100%
	30.0	Scratches	0	Bright Light, 100% (note 2)
	31.0	Haze	none	Bright Light, 100% (note 2)

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

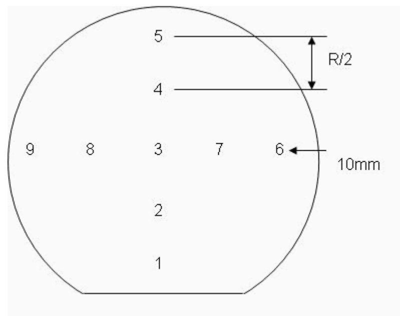
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information